NPN Epitaxial Planar Silicon Transistor



15C01SS

Low-Frequency General-Purpose Amplifier Applications

Applications

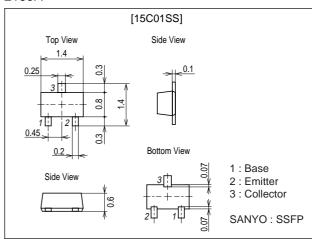
• Low-frequency Amplifier, muting circuit.

Features

- Large current capacitance.
- Low collector-to-emitter saturation voltage (resistance). RCE (sat) typ.= 0.58Ω [IC=0.7A, IB=35mA].
- Ultrasmall, slim flat-lead package (1.4mm×0.8mm×0.6mm).
- Small ON-resistance (Ron).

Package Dimensions

unit : mm 2159A



Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		20	V
Collector-to-Emitter Voltage	VCEO		15	V
Emitter-to-Base Voltage	VEBO		5	V
Collector Current	IC		600	mA
Collector Current (Pulse)	ICP		1.2	А
Collector Dissipation	PC	Mounted on a glass epoxy board (20×30×1.6mm)	200	mW
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector Cutoff Current	ICBO	V _{CB} =15V, I _E =0			0.1	μΑ
Emitter Cutoff Current	IEBO	VEB=4V, IC=0			0.1	μA
DC Current Gain	hFE	V _{CE} =2V, I _C =10mA	300		800	
Gain-Bandwidth Product	fT	V _{CE} =2V, I _C =50mA		330		MHz
Output Capacitance	Cob	V _{CB} =10V, f=1MHz		3.2		pF
Collector-to-Emitter Saturation Voltage	V _{CE} (sat)	IC=200mA, IB=10mA		150	300	mV
Base-to-Emitter Saturation Voltage	V _{BE} (sat)	IC=200mA, IB=10mA		0.9	1.2	V
forking · VP						

Marking : YP

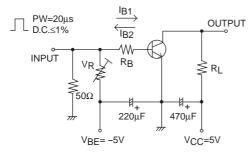
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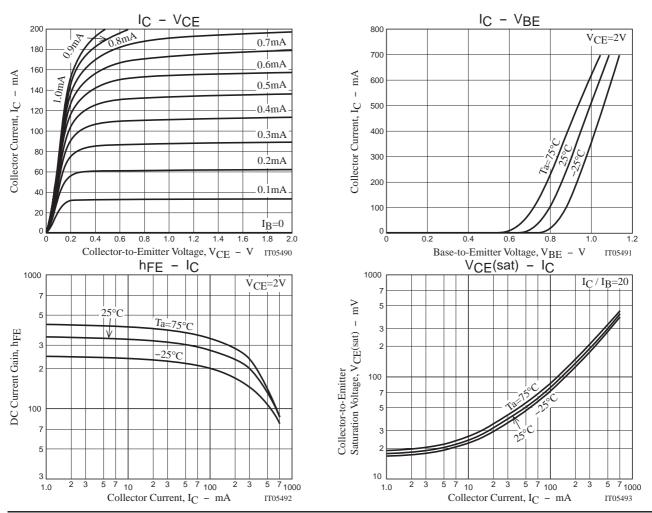
SANYO Electric Co., Ltd. Semiconductor Company TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN Continued from preceding page.

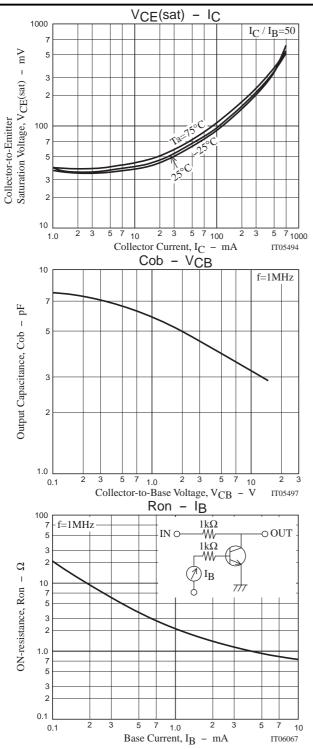
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector-to-Base Breakdown Voltage	V(BR)CBO	IC=10μA, IE=0	20			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	IC=1mA, R _{BE} =∞	15			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	IE=10μA, IC=0	5			V
Turn-ON Time	ton	See specified Test Circuit.		30		ns
Storage Time	tstg	See specified Test Circuit.		77		ns
Fall Time	tf	See specified Test Circuit.		40		ns

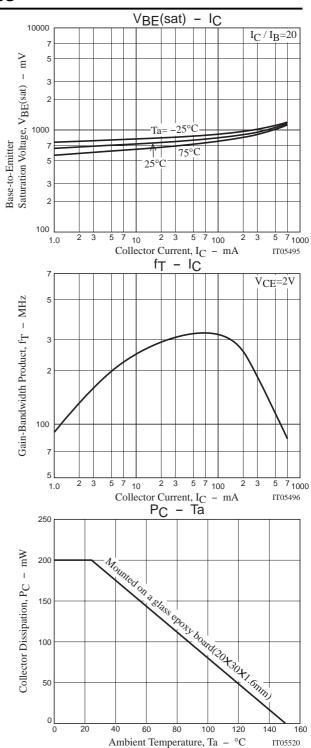
Switching Time Test Circuit



IC=20IB1= -20IB2=500mA







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